

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0029] as follows:

[0029] Gated storage node 306 is conductively coupled to a shutter gate transistor 304 activated by control signal SGH. Storage node 306 is also coupled between barrier region 308, p+ region 440 and transfer transistor 310. Barrier layer is, for example, a boron layer that is implanted between photodiode 302 and storage node 306 to control charge transference from photodiode 302 to storage node 306. Tying barrier region 308 to shutter gate transistor 304 decreases barrier region 308 and allows charge transfer from photodiode 302 to storage node 306 when shutter transistor 304 is activated by SGH. As depicted in FIG. 4, barrier region 308 and storage node 306 are made up of oppositely doped silicon. Exemplary structure and operation of pixels employing a gated storage node between a photodiode 302 and a floating diffusion region 322 is described in commonly-assigned application serial no. 10/XXX,XXX 10/721,191, filed [[_____]] May 26, 2005, the entire ~~content~~ contents of which [[is]] are incorporated herein by reference. Further, exemplary structure and operation of pixels employing a storage capacitor between a photodiode and a floating diffusion region is described in commonly assigned application serial no. 10/XXX,XXX 10/721,190, filed [[_____]] May 26, 2005, the entire ~~content~~ contents of which [[is]] are incorporated herein by reference.